

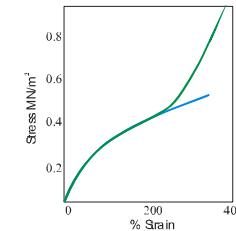
Lecture 13

Ch 10 Rubber Elasticity + Ch 6 Defects (vacancy) L1

F 22.08.2025

1

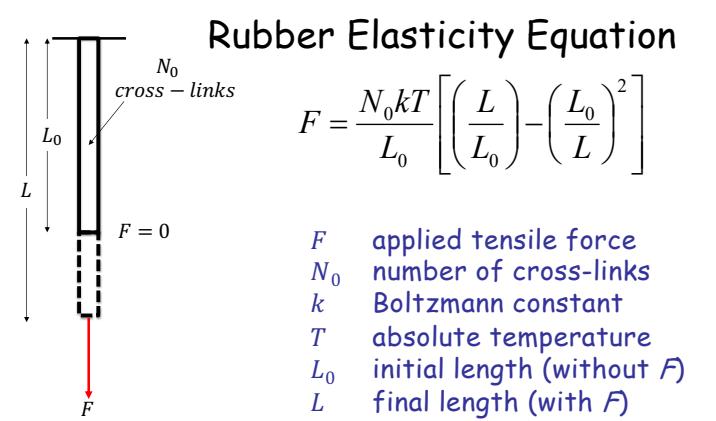
Elastomer
Polymers with very extensive elastic deformation



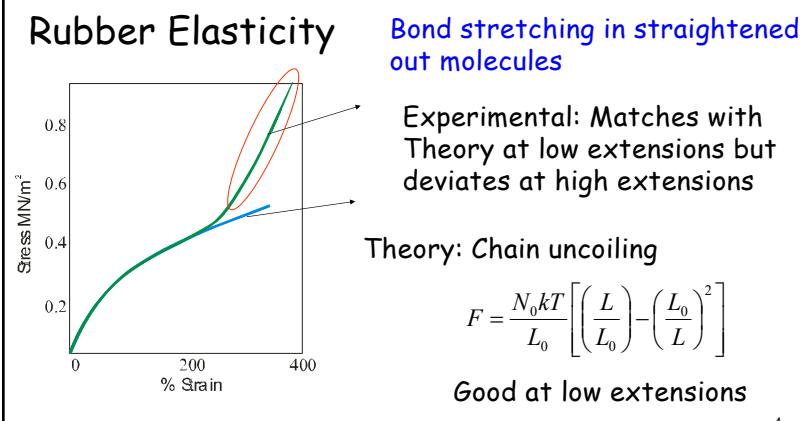
Stress-strain relationship is non-linear

Example: Rubber

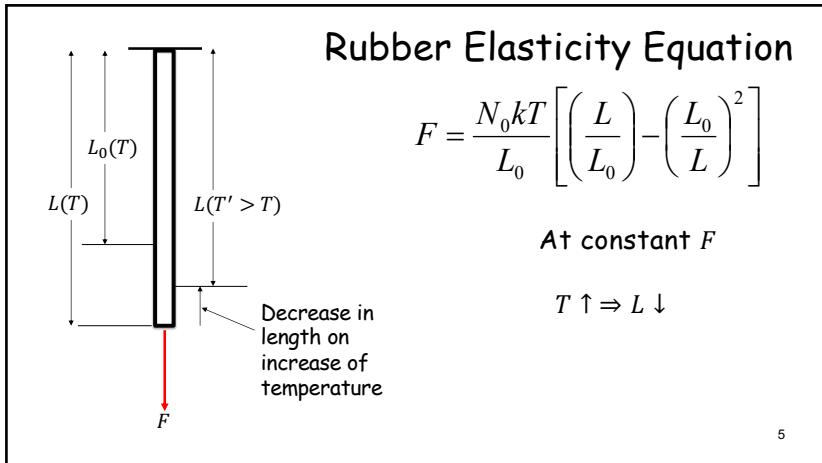
2



3



4



5

Elastomers have -ve thermal expansion coefficient, i.e., they **CONTRACT** on heating!!

EXPERIMENT 8

Section 10.3 of the textbook

6

Crystal Defects

Chapter 6

7

Crystal = Lattice + Motif

Is a lattice finite or infinite?

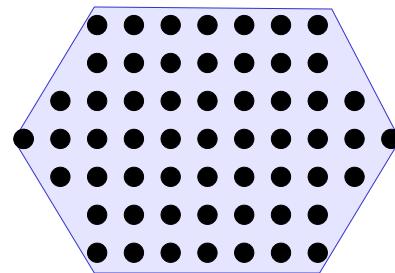
Is a lattice finite or infinite?

Abrupt ending of crystal at free surface

Free surface of a crystal is a defect

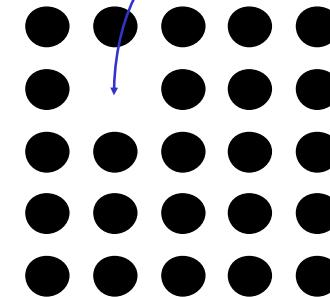
8

Free surface: a 2D defect



9

Vacancy: A point defect



10

Defects Dimensionality Examples

Point	0	Vacancy
Line	1	Dislocation
Surface	2	Free surface, Grain boundary Stacking Fault

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Point Defects

Vacancy

12

Point Defects: vacancy

A Guess

There **may** be some vacant sites in a crystal

Surprising Fact

There **must** be a certain fraction of vacant sites in a crystal in **equilibrium**.

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Equilibrium?

Equilibrium means Minimum Gibbs free energy G at constant T and P

A crystal with vacancies has a lower free energy G than a perfect crystal

What is the equilibrium concentration of vacancies?

14

Gibbs Free Energy G ?

$$G = H - TS \quad T \text{ Absolute temperature}$$

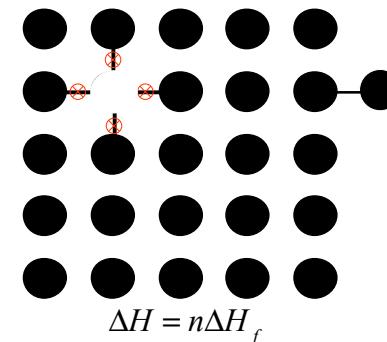
H ?

1. Enthalpy $H = E + PV$ E internal energy
 P pressure
 V volume

2. Entropy $S = k \ln W$ k Boltzmann constant
 W number of microstates

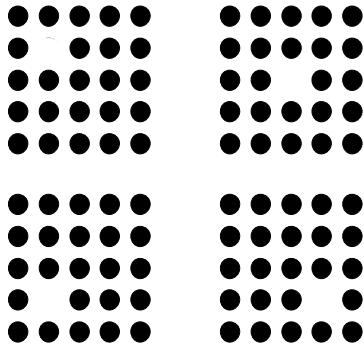
15

Vacancy increases H of the crystal due to energy required to break bonds



16

Vacancy increases S of the crystal due to configurational entropy



17

Configurational entropy due to vacancy

Number of atoms: N

Number of vacancies: n

Total number of sites: $N+n$

The number of microstates:

$$W = {}^{N+n}C_n = \frac{(N+n)!}{n!N!}$$

Increase in entropy S due to vacancies:

$$\Delta S = k \ln W = k \ln \frac{(N+n)!}{n! N!} = k [\ln(N+n)! - \ln n! - \ln N!]$$

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Stirlings Approximation

$$\ln N! \approx N \ln N - N$$

N	$\ln N!$	$N \ln N - N$
1	0	-1
10	15.10	13.03
100	363.74	360.51

19

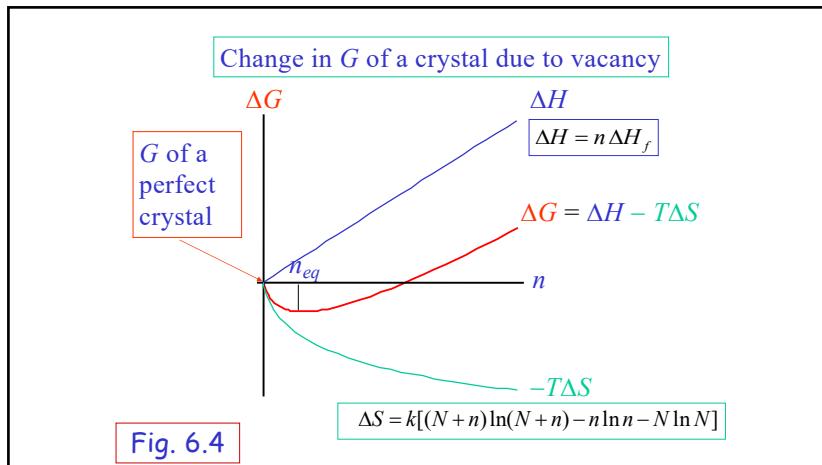
$$\Delta S = k \ln W = k[\ln(N+n)! - \ln n! - \ln N!]$$

$$\ln N! \approx N \ln N - N$$

$$\Delta S = k[(N+n)\ln(N+n) - n\ln n - N\ln N]$$

$$\Delta H = n \Delta H_f$$

20



21

Equilibrium concentration of vacancy

$$\Delta S = k[(N+n)\ln(N+n) - n\ln n - N\ln N]$$

$$\Delta H = n \Delta H_f$$

$$\Delta G = n\Delta H_f - Tk[(N+n)\ln(N+n) - n\ln n - N\ln N]$$

$$\frac{\partial \Delta G}{\partial n} \bigg|_{n=n_{eq}} = 0$$

$$\frac{n_{eq}}{N} = \exp\left(-\frac{\Delta H_f}{kT}\right)$$

With $n_{eq} \ll N$

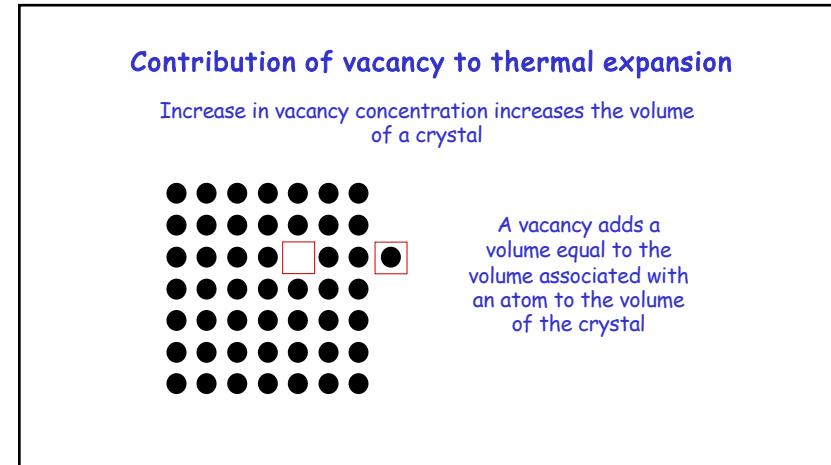
22

$$\frac{n_{eq}}{N} = \exp\left(-\frac{\Delta H_f}{kT}\right)$$

Al: $\Delta H_f = 0.70$ ev/vacancy
 Ni: $\Delta H_f = 1.74$ ev/vacancy

n/N	0 K	300 K	900 K
Al	0	1.45×10^{-12}	1.12×10^{-4}
Ni	0	5.59×10^{-30}	1.78×10^{-10}

23



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Contribution of vacancy to thermal expansion

Thus vacancy makes a small contribution to the thermal expansion of a crystal

Thermal expansion =

lattice parameter expansion

+

Increase in volume due to vacancy

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Contribution of vacancy to thermal expansion

$$V = Nv$$

V=volume of crystal
v= volume associated with
one atom
N=no. of sites
(atoms+vacancy)

$$\frac{\Delta V}{V} = \frac{\Delta v}{v} + \frac{\Delta N}{N}$$

Total
expansion

Lattice
parameter
increase

vacancy

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Experimental determination of n/N

$$\frac{\Delta V}{V} = \frac{\Delta v}{v} + \frac{\Delta N}{N}$$

$$\frac{3\Delta L}{L} = \frac{3\Delta a}{a} + \frac{n}{N}$$

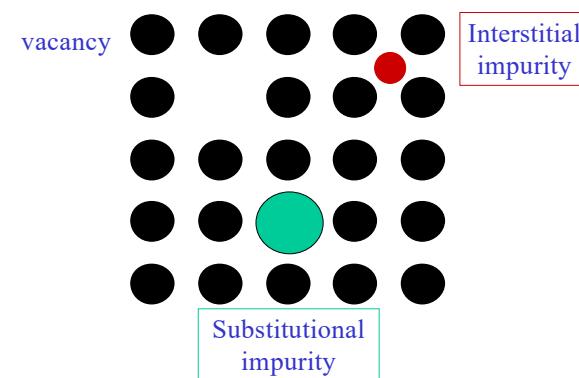
$$\frac{n}{N} = 3 \left(\frac{\Delta L}{L} - \frac{\Delta a}{a} \right)$$

Linear thermal expansion coefficient Lattice parameter as a function of temperature XRD

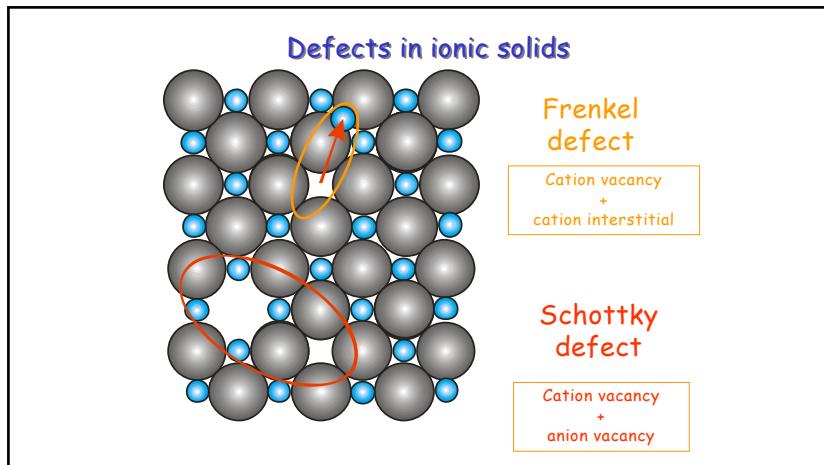
Problem
6.2

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Point Defects



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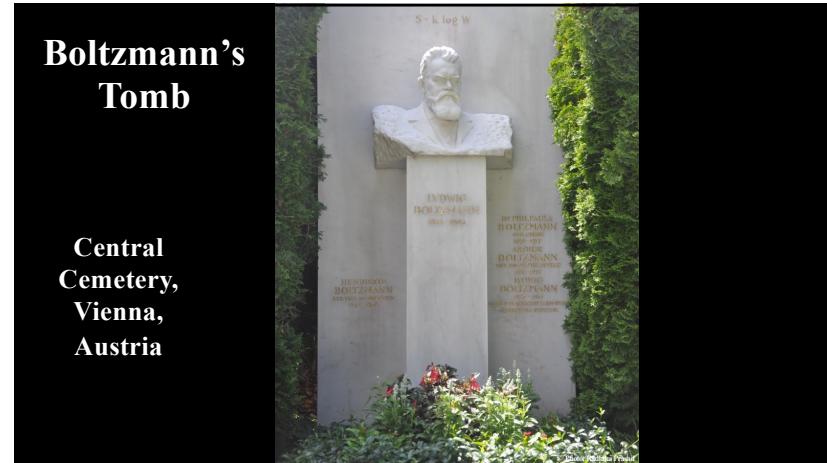
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Atomic
or
statistical
interpretation of entropy

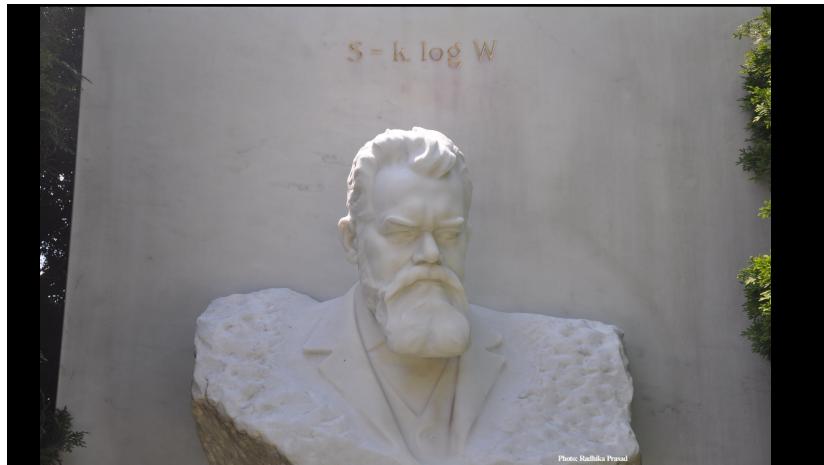
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32



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Boltzmann's Epitaph

$$S = k \ln W$$

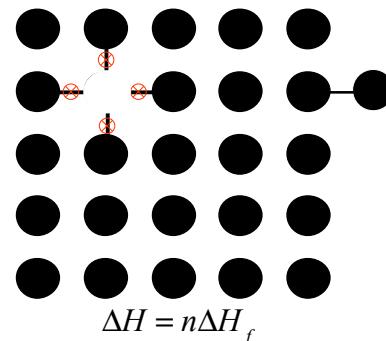
(2.5)

W is the number of microstates corresponding to a given macrostate



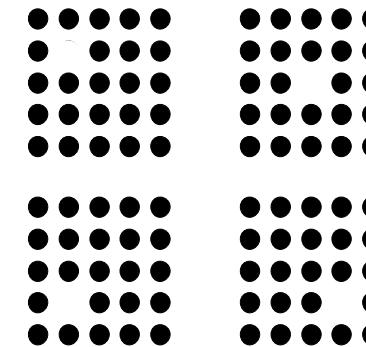
34

Vacancy increases H of the crystal due to energy required to break bonds



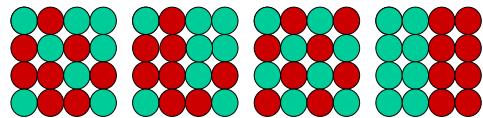
35

Vacancy increases S of the crystal due to configurational entropy



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$$W = {}^N C_n = \frac{N!}{n!(N-n)!} \quad (2.9)$$



$N=16, n=8, W=12,870$

37

Stirlings Approximation

$$\ln N! \approx N \ln N - N$$

N	$\ln N!$	$N \ln N - N$
1	0	-1
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39

Configurational entropy due to vacancy

Number of atoms: N

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Total number of sites: $N+n$

The number of microstates:

$$W = {}^{N+n}C_n = \frac{(N+n)!}{n!N!}$$

Increase in entropy S due to vacancies:

$$\Delta S = k \ln W = k \ln \frac{(N+n)!}{n!N!} = k[\ln(N+n)! - \ln n! - \ln N!]$$

38

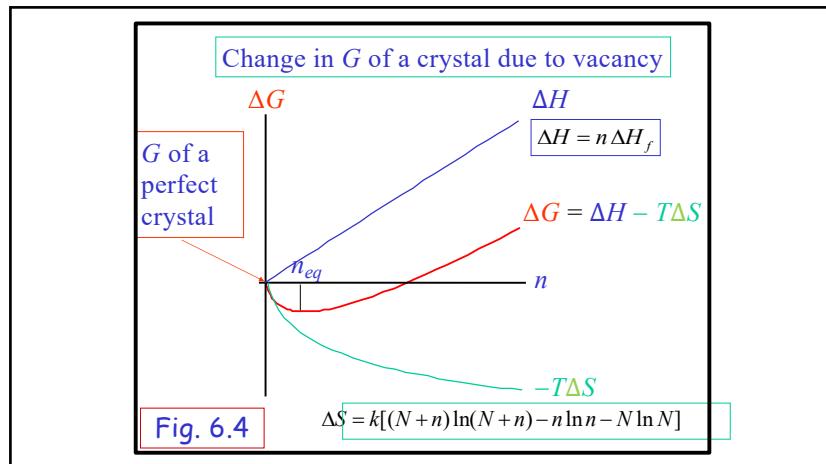
$$\Delta S = k \ln W = k[\ln(N+n)! - \ln n! - \ln N!]$$

$$\ln N! \approx N \ln N - N$$

$$\Delta S = k[(N+n)\ln(N+n) - n\ln n - N\ln N]$$

$$\Delta H = n \Delta H_f$$

40



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Equilibrium concentration of vacancy

$$\Delta S = k[(N+n)\ln(N+n) - n\ln n - N\ln N]$$

$$\Delta H = n \Delta H_f$$

$$\Delta G = n \Delta H_f - T k[(N+n)\ln(N+n) - n\ln n - N\ln N]$$

$$\frac{\partial \Delta G}{\partial n} \bigg|_{n=n_{eq}} = 0$$

$$\frac{n_{eq}}{N} = \exp\left(-\frac{\Delta H_f}{kT}\right)$$

With $n_{eq} \ll N$

42

$$\frac{n_{eq}}{N} = \exp\left(-\frac{\Delta H_f}{kT}\right)$$

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43

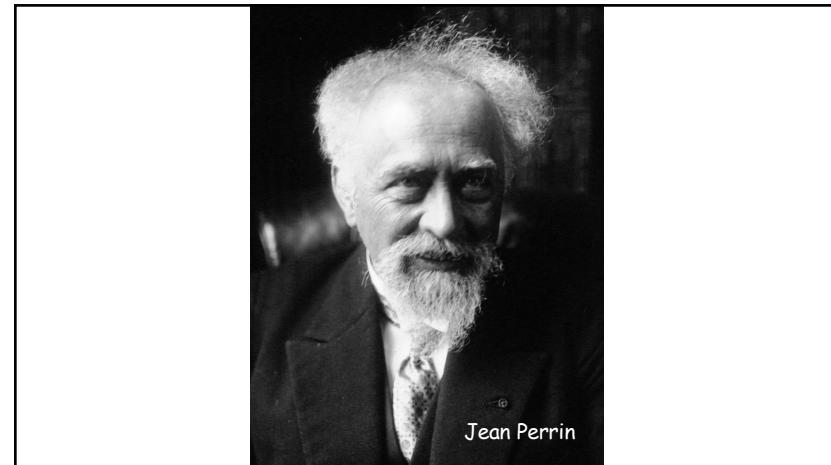
$$\frac{n_{eq}}{N} = \exp\left(-\frac{\Delta H_f}{kT}\right) \quad \Delta H_f \quad \text{per vacancy}$$

$$\frac{n_{eq}}{N} = \exp\left(-\frac{\Delta H_f}{RT}\right) \quad \Delta H_f \quad \text{per mole of vacancy}$$

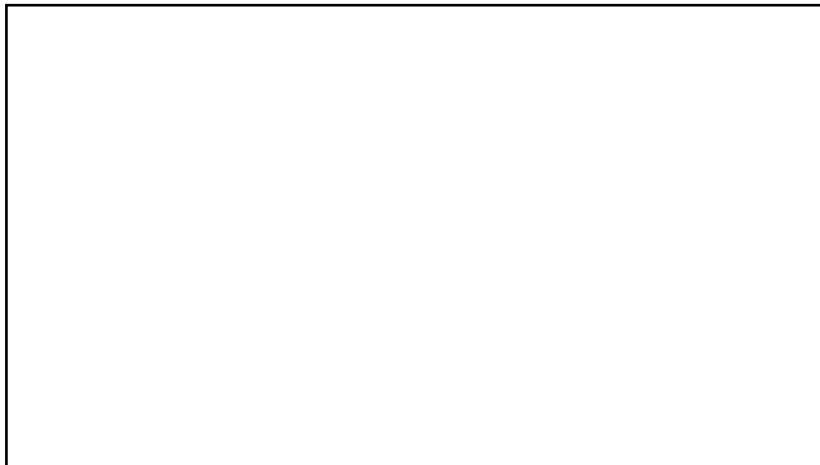
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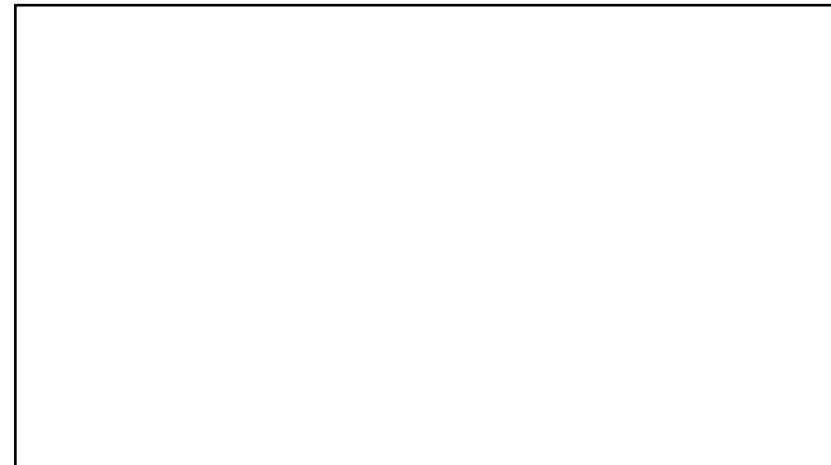
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Lecture 14
+
Ch 6 Defects L2: Dislocations

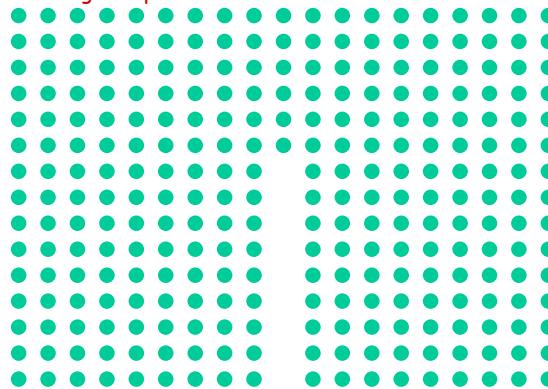
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Line Defects Dislocations

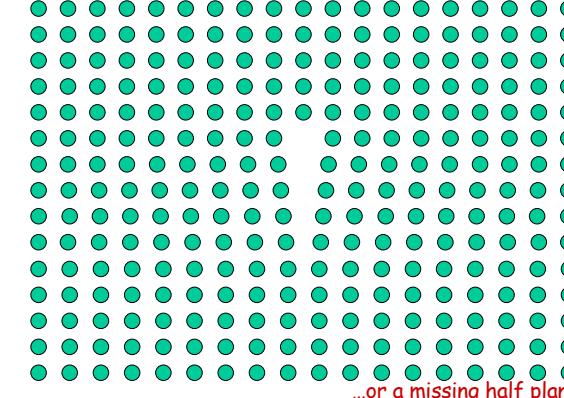
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Missing half plane → A Defect



51

An extra half plane...



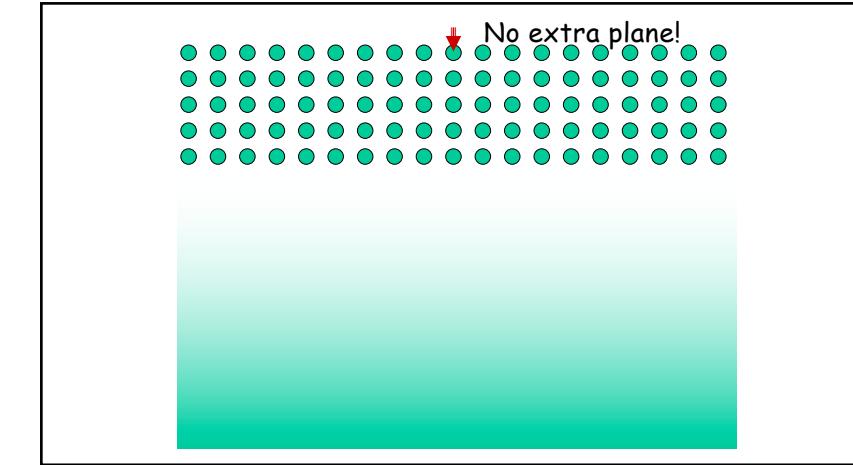
52

What kind of defect is this?

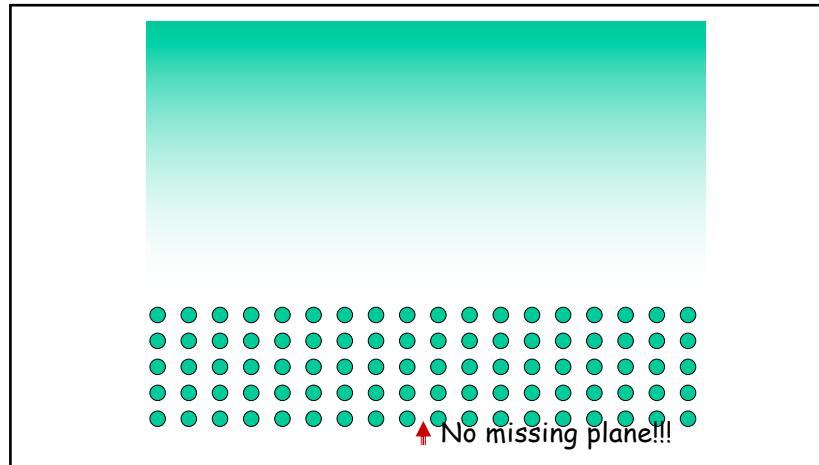
A line defect?

Or a planar defect?

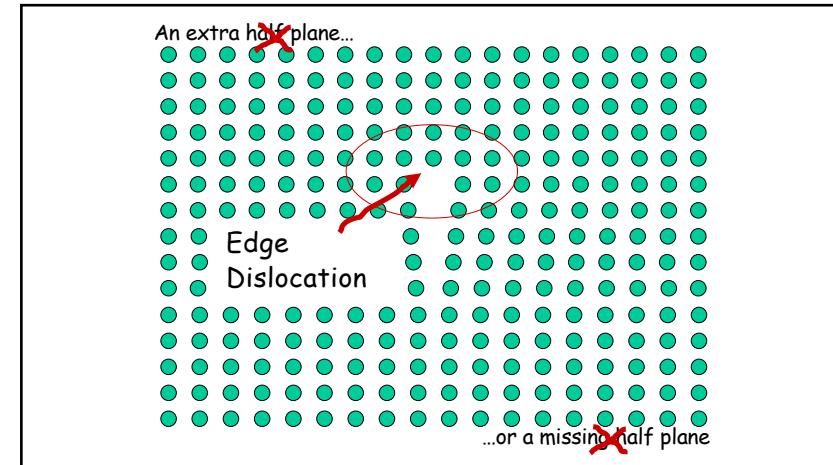
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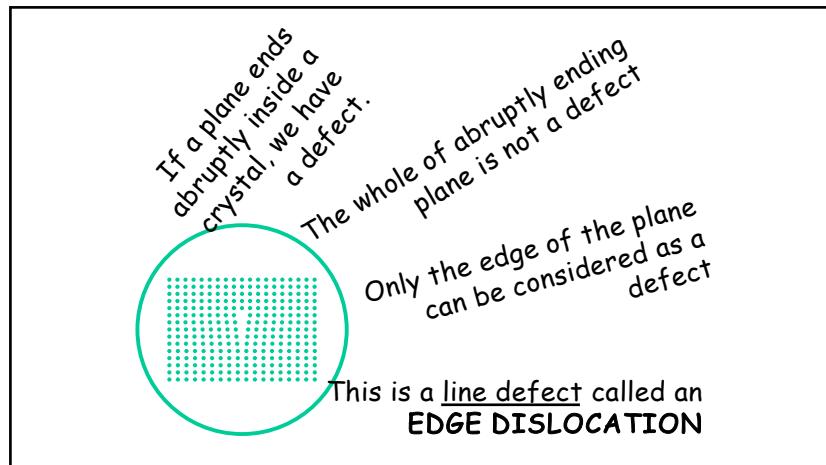
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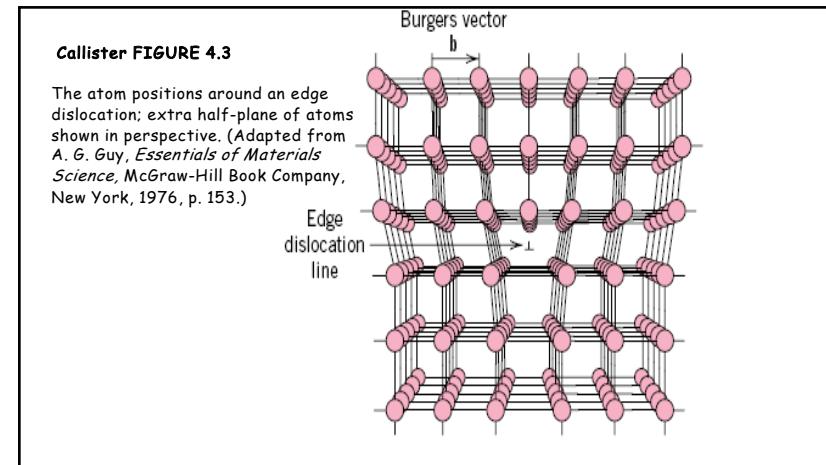
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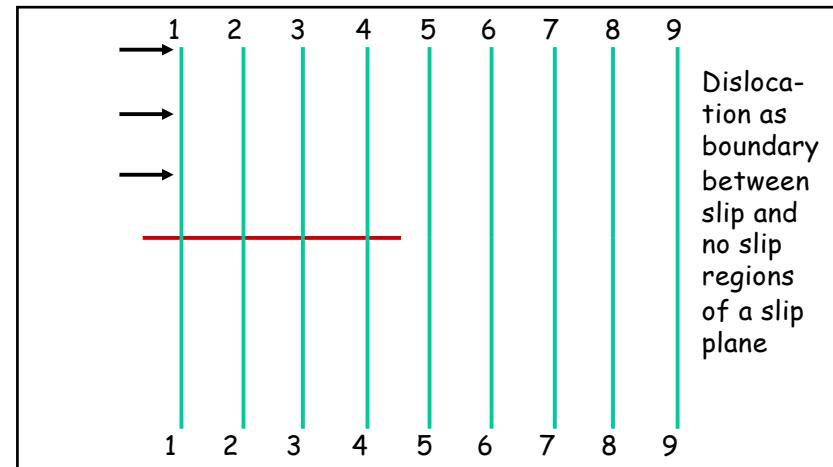
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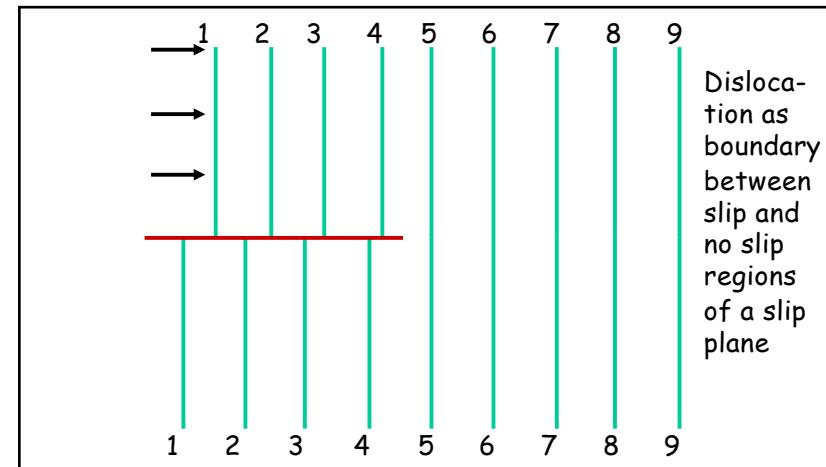
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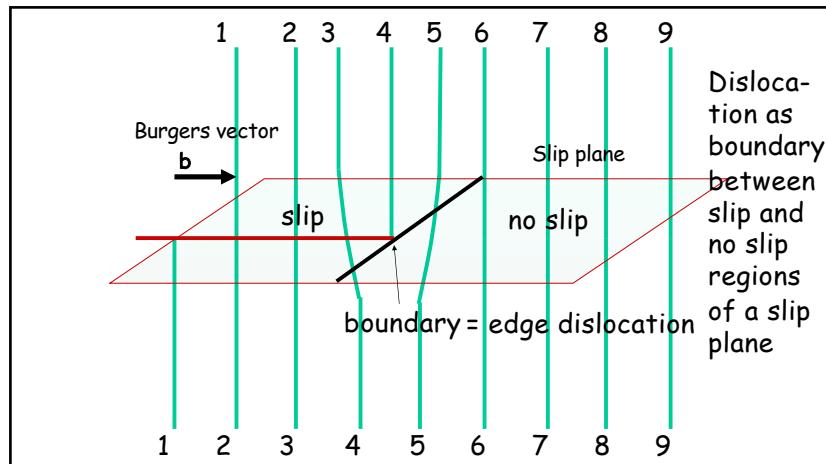
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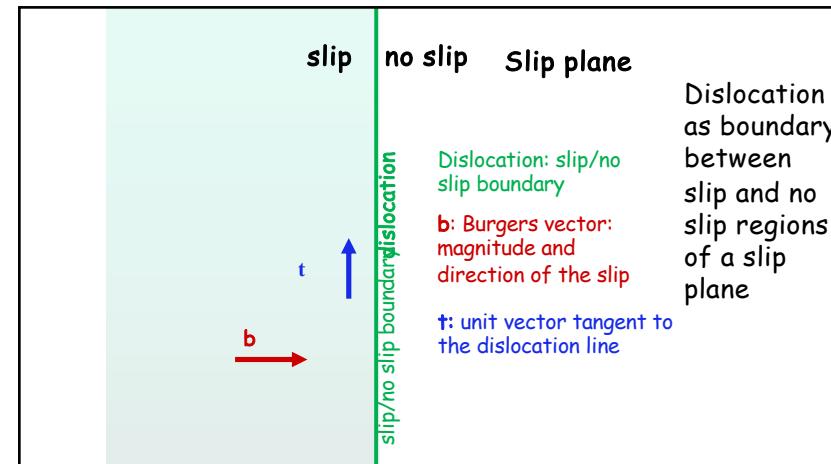
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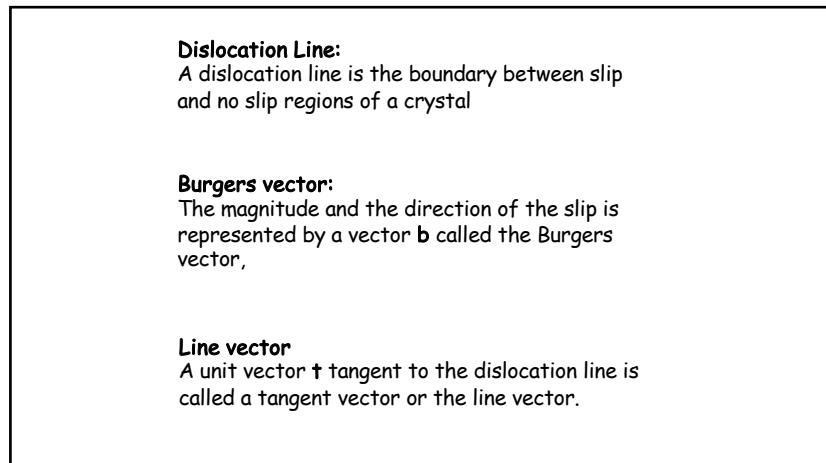
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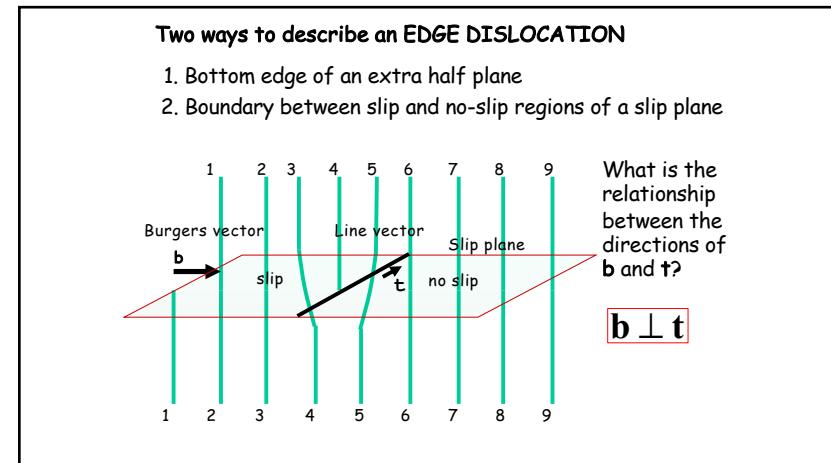
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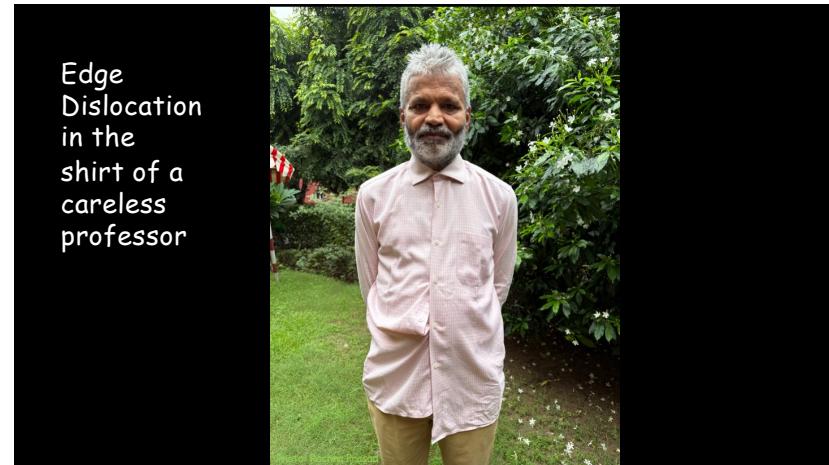
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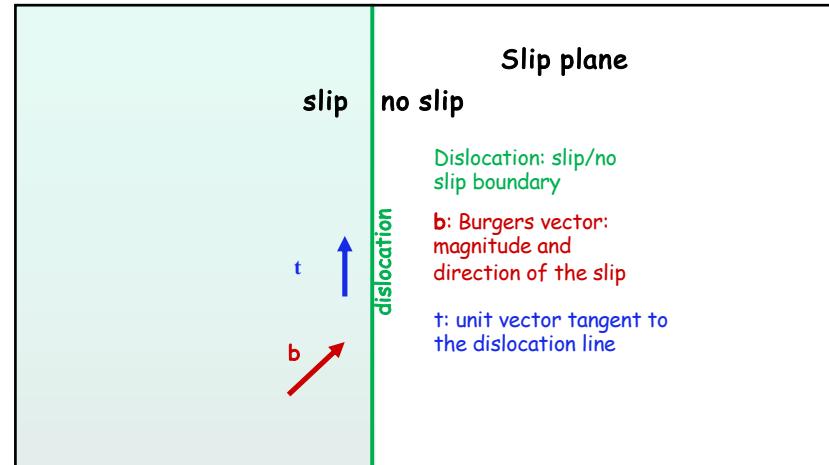
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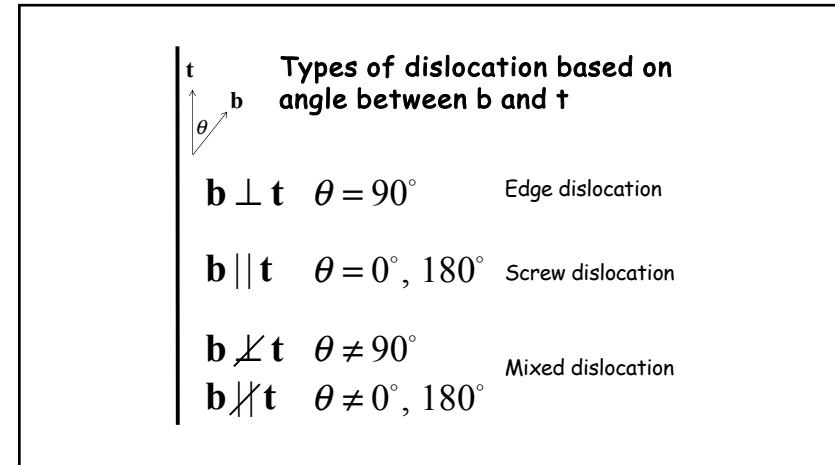
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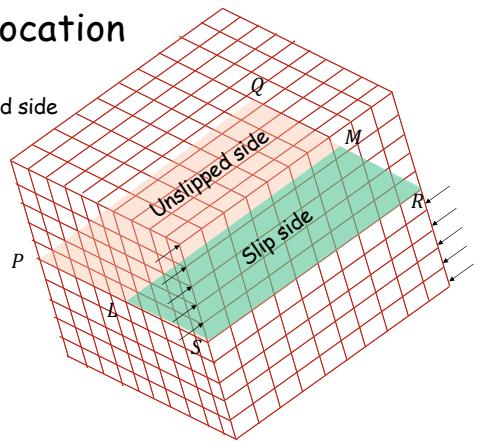


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An RH screw dislocation

PQRS: Slip plane

LMRS: Slip side LPQM: Unslipped side



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An RH screw dislocation

PQRS: Slip plane

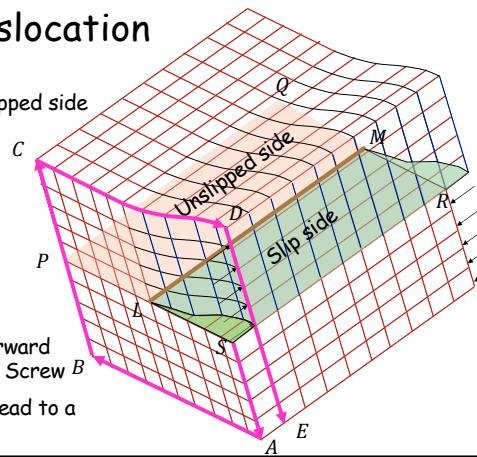
LMRS: Slip side LPQM: Unslipped side

LM: Boundary between
slipped and unslipped side
≡ Dislocation Line

Distinct \parallel planes \perp to the
dislocation line have become a
single helicoidal surface like
that of a screw

Clockwise rotation leads to forward
movement: Right-Handed (RH) Screw B

Slip in opposite direction will lead to a
left-handed screw.



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	Positive	Negative
Edge Dislocation	Extra half plane above the slip plane	Extra half plane below the slip plane
	⊥	⊤
Screw Dislocation	Left-handed	Right-handed
	Left-handed screw	Right-handed screw
	⟳	⟲

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Lecture 15

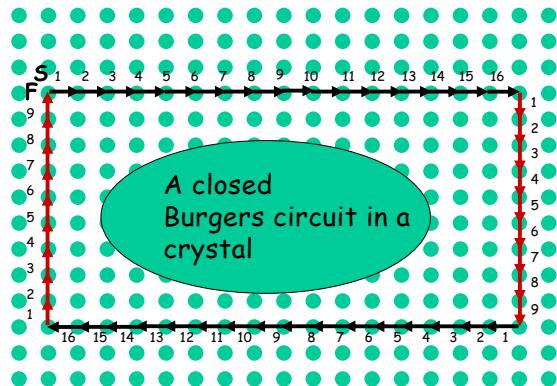
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Ch 6 Defects L3: Dislocations

W 27.08.2025

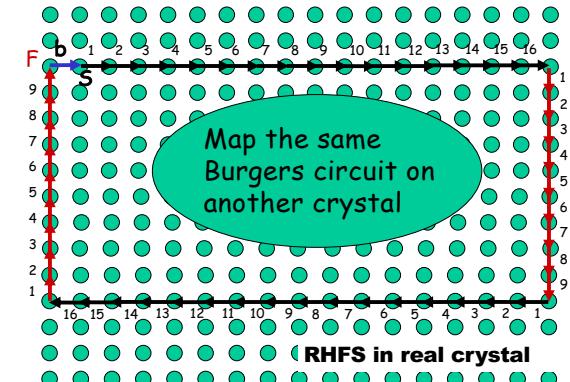
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Burgers Circuit



73

The Burgers circuit fails to close !!



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Two interpretations of Burgers Vector

Magnitude and direction of slip

Closure failure of a Burgers circuit

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Burgers vector



~~Burger's vector~~



Johannes Martinus
BURGERS

~~Burgers vector~~

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Burgers Circuit and Burgers Vector

Circuit closed in an ideal crystal, **Or vice-versa**
 Fails to close in a real crystal

The closure failure \rightarrow dislocation

Finish to Start vector \rightarrow Burgers vector

Or Start to Finish

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Attendance on

<https://rollcall.iitd.ac.in>

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Conventions for Burgers vector

Closure failure: **Real crystal** or Ideal crystal

RH or LH

MLL100
RHFS Real Crystal

F-S or **S-F**

$2 \times 2 \times 2 = 8$ conventions

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b for an RH screw dislocation

PQRS: Slip plane

LMRS: Slip side LPQM: Unslipped side

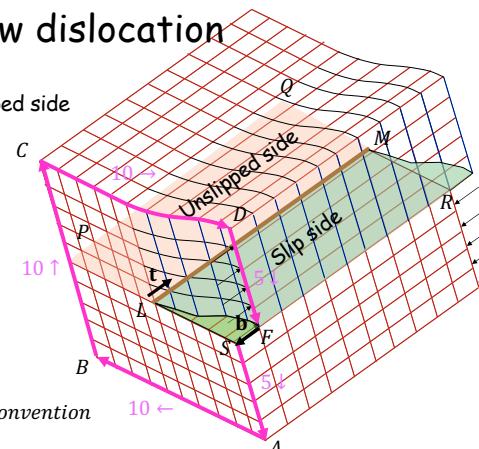
LM: Boundary between
 slipped and unslipped side
 \equiv Dislocation Line

t: tangent vector

SABCDF: RH Burgers circuit wrt to **t**

FS: Burgers Vector **b**

b = $-bt$ *in our RHFS convention*



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Two equivalent classes of \mathbf{b} conventions

For RH screw dislocation

$$\mathbf{b} = -\mathbf{bt}$$

\mathbf{b} antiparallel to \mathbf{t}

$$\mathbf{b} = \mathbf{bt}$$

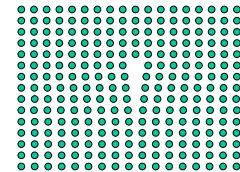
\mathbf{b} parallel to \mathbf{t}

RHFS convention of MLL100

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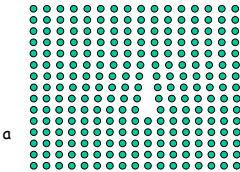
Two types of edge dislocations

+ve (\perp)



Half plane above the slip plane

-ve (\top)

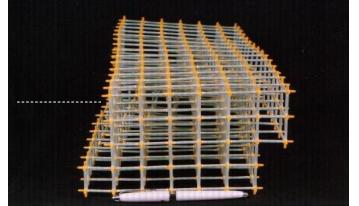


Half plane below the slip plane

You can rotate a +ve edge dislocation to become a -ve edge dislocation



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Prof. S. Ranganathan
IISc, Bangalore

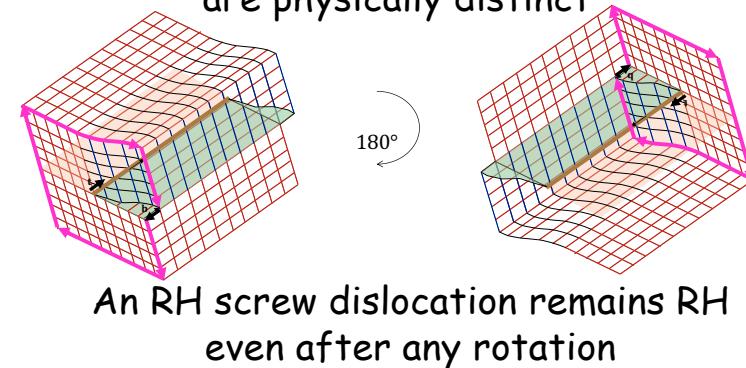
SR: Is this an RH or LH dislocation?

RP: Sir, that depends upon the way you look at it.

Conference on Perspectives in Physical Metallurgy and Materials Science,
Indian Institute of Science, Bangalore, 12-14 July, 2001.
R. Prasad, "Dislocation Models for Classroom Demonstrations"

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RH and LH Screw dislocations are physically distinct



84

Positive and negative edge dislocations can be superimposed on each other by 180° rotation about the dislocation line

LH and RH screw dislocations cannot be superimposed on each other by rotation.

They can be superimposed on each other by a reflection. Hence, they are chiral pair.

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Slip Plane

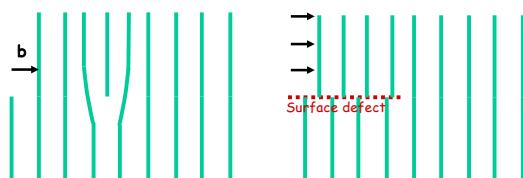
A plane containing b and t is called the slip plane of the dislocation line.

Edge dislocation: $b \perp t \Rightarrow$ A unique slip plane

Screw dislocation: $b \parallel t \Rightarrow$ Non unique slip planes: Any plane passing through both b and t is possible slip plane

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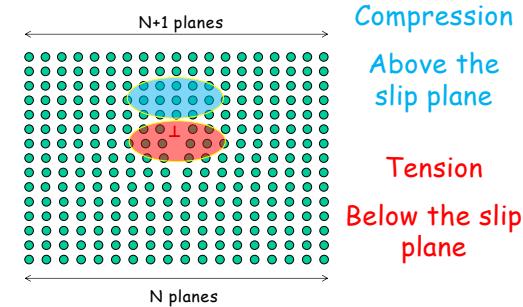
b is a lattice translation



If b is not a complete lattice translation then a surface defect (stacking fault) will be associated along with the line defect.

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Elastic strain field associated with an edge dislocation



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Line energy of a dislocation

Elastic energy per unit length of a dislocation line

$$E = \frac{1}{2} \mu b^2$$

μ Shear modulus of the crystal
 b Length of the Burgers vector

Unit: J m^{-1}

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b is the shortest lattice translation

Energy of a dislocation line
is proportional to b^2 . $E = \frac{1}{2} \mu b^2$

Thus dislocations with
short b are preferred.

b is a lattice translation

b is the shortest lattice
translation

90

b is the shortest lattice
translation

SC	$\langle 100 \rangle$
BCC	$\frac{1}{2} \langle 111 \rangle$
FCC	$\frac{1}{2} \langle 110 \rangle$
DC	$\frac{1}{2} \langle 110 \rangle$
NaCl	$\frac{1}{2} \langle 110 \rangle$
CsCl	$\langle 100 \rangle$

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